

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTORNEY DOCKET NO.
M122-2274SERIAL NO.
10/806,923LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

APPLICANT: Weimin Li et al.

FILING DATE
March 22, 2004GROUP ART UNIT
2842-2891

U.S. PATENT DOCUMENTS

| Examiner's Initials | | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate |
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| | AG | 5,719,085 | 02/1998 | Moon et al. | | | |
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| AKS | AJ | 02277253A | 11/1990 | Japan (Hayashide et al.) | | | | |
| | AK | 146224 | 01/1996 | Japan | | | | |
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Asst. Examiner Sarhar 11/4/05

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| | | FILING DATE March 22, 2004 | GROUP ART UNIT 2812 2891 |

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| Asok | Anuman Sarthar 11/4/05 | | |
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| | | | Silanol, 397 THIN SOLID FILMS 78-82 (2001). | | | | | |
| EXAMINER | | DATE CONSIDERED | | | | | | |
| | | <div style="display: flex; justify-content: space-between;"> Ashu Kumar Sankar 11/4/2005 </div> | | | | | | |
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| AKS | AM | | Hausmann et al., "Catalytic vapor deposition of highly conformal silica nanolaminates", Department of | | | | | |
| | | | Chemistry and Chemical Biology, Harvard University, May 14, 2002, pp. 1-13. | | | | | |
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Sheet 1 of 2

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| | AD | 2002/0018849 | 2/2002 | George et al. | | | |
| | AE | 2003/0032281 A1 | 2/13/2003 | Werkhoven et al. | | | |
| | AF | 2003/00129826 A1 | 7/10/2003 | Werkhoven et al. | | | |
| | AG | 2004/0209484 | 10/2004 | Hill et al. | | | |
| AKS | AH | 2004/0266153 A1 | 12/30/2004 | Yongjun Jeff Hu | | | |

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| AKS | AI | EP 0817251 A | 1/1998 | EPO | | | |
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| AKS | AK | PCT/US2004/021156; Filed 6/30/2004; Search Report. | | | |
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Sheet 2 of 2

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